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S/N 10/765,619

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et.al. Examiner: Asok K. Sarkar
Serial No.: 10/765,619 Group Art Unit: 2829
Filed: January 27, 2004 Docket: 1303.033US2
Title: HIGH-QUALITY PRASEODYMIUM GATE DIELECTRICS (As Amended)

COMMUNICATION CONCERNING RELATED APPLICATION(S)

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date</u>	<u>Attorney Docket</u>	<u>Title</u>
10/768597	January 30, 2004	1303.033US3	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
10/789042	February 27, 2004	1303.050US2	ATOMIC LAYER-DEPOSITED LaAlO ₃ FILMS FOR GATE DIELECTRICS
11/036296	January 14, 2005	1303.030US2	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN CoTiO ₃ GATE DIELECTRICS
10/789044	February 27, 2004	1303.070US2	LANTHANIDE DOPED TiO _x DIELECTRIC FILMS
10/863953	June 9, 2004	1303.031US2	HIGHLY RELIABLE AMORPHOUS HIGH-k GATE DIELECTRIC ZrO _x Ny
10/930138	August 31, 2004	1303.044US2	EVAPORATION OF Y-Si-O FILMS FOR MEDIUM-k DIELECTRICS
10/930184	August 31, 2004	1303.021US2	CRYSTALLINE OR AMORPHOUS MEDIUM-K GATE OXIDES, Y ₂ O ₃ AND GD ₂ O ₃
10/930516	August 31, 2004	1303.078US2	ATOMIC LAYER DEPOSITED HfSiON DIELECTRIC FILMS

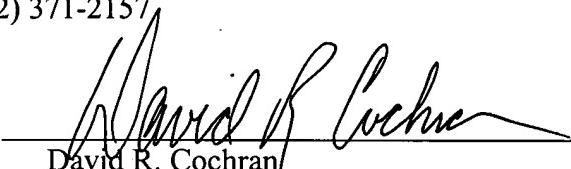
10/931341	August 31, 2004	1303.082US2	ATOMIC LAYER DEPOSITED ZR-SN-TI-O FILMS USING TiI4
10/930431	August 31, 2004	1303.056US2	ATOMIC LAYER-DEPOSITED HfAlO3 FILMS FOR GATE DIELECTRICS
10/931365	August 31, 2004	1303.059US2	Pr2O3-BASED La-oxide GATE DIELECTRICS
10/931364	August 31, 2004	1303.069US2	LANTHANIDE DOPED TiOx DIELECTRIC FILMS BY PLASMA OXIDATION
10/931343	August 31, 2004	1303.101US2	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS
10/931340	August 31, 2004	1303.107US2	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS
10/931356	August 31, 2004	1303.026US2	HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO2
	February 15, 2005	1303.133US1	ATOMIC LAYER DEPOSITION OF Zr3N4/ZrO2 FILMS AS GATE DIELECTRICS
11/031289	January 7, 2005	1303.069US3	LANTHANIDE DOPED TiOx DIELECTRIC FILMS BY PLASMA OXIDATION
	February 16, 2005	1303.046US2	EVAPORATED LaAlO3 FILMS FOR GATE DIELECTRICS

Respectfully submitted,

KIE Y. AHN ET AL.

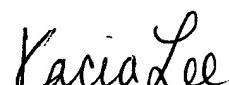
By Applicants' Representatives,

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Date 21 February 2005 By 
David R. Cochran
Reg. No. 46,632

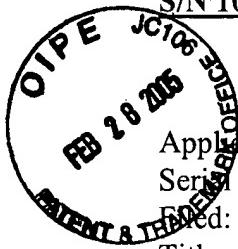
CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 22 day of February, 2005.

KACIA LEE
Name


Signature

S/N 10/765,619

PATENT



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al. Examiner: Asok K Sarkar
Serial No.: 10/765,619 Group Art Unit: 2829
Filed: January 27, 2004 Docket: 1303.033US2
Title: HIGH-QUALITY PRASEODYMIUM GATE DIELECTRICS (As Amended)

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. § 1.97(c)(2), Applicants have included the fee of \$180.00 as set forth in 37 C.F.R. § 1.17(p). Please charge any additional fees or credit any overpayment to Deposit Account No. 19-0743.

03/01/2005 EAREGAY1 00000003 10765619

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180.00 0P

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Pursuant to 37 C.F.R. 1.98(a)(2), Applicant believes that copies of cited U.S. Patents and Published Applications are no longer required to be provided to the Office. Notification of this change was provided in the United States Patent and Trademark Office OG Notices dated October 12, 2004. Thus, Applicant has not included copies of any US Patents or Published Applications cited with this submission. Should the Office require copies to be provided, Applicant respectfully requests that notice of such requirement be directed to Applicant's below-signed representative. Applicant acknowledges the requirement to submit copies of foreign patent documents and non-patent literature in accordance with 37 C.F.R. 1.98(a)(2).

Respectfully submitted,

KIE Y. AHN ET AL.

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
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(612) 371-2157

Date 22 February 2005

By David R. Cochran
David R. Cochran
Reg. No. 46,632

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 22 day of February, 2005.

Name KACIA LEE

Signature Kacia Lee

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Use as many sheets as necessary)
*Complete if Known*

Application Number	10/765,619
Filing Date	January 27, 2004
First Named Inventor	Ahn, Kie
Group Art Unit	2829
Examiner Name	Sarkar, Asok

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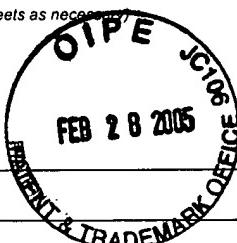
Attorney Docket No: 1303.033US2

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EXAMINER**DATE CONSIDERED**

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete if Known <table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 50%; padding: 2px;">Application Number</td> <td style="width: 50%; padding: 2px;">10/765,619</td> </tr> <tr> <td style="padding: 2px;">Filing Date</td> <td style="padding: 2px;">January 27, 2004</td> </tr> <tr> <td style="padding: 2px;">First Named Inventor</td> <td style="padding: 2px;">Ahn, Kie</td> </tr> <tr> <td style="padding: 2px;">Group Art Unit</td> <td style="padding: 2px;">2829</td> </tr> <tr> <td style="padding: 2px;">Examiner Name</td> <td style="padding: 2px;">Sarkar, Asok</td> </tr> </table>		Application Number	10/765,619	Filing Date	January 27, 2004	First Named Inventor	Ahn, Kie	Group Art Unit	2829	Examiner Name	Sarkar, Asok
Application Number	10/765,619												
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First Named Inventor	Ahn, Kie												
Group Art Unit	2829												
Examiner Name	Sarkar, Asok												
Sheet 2 of 2		Attorney Docket No: 1303.033US2											



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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²

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